Schottky Barrier Diode in a TO-220 Plastic Package.

Low power loss, high efficiency.

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

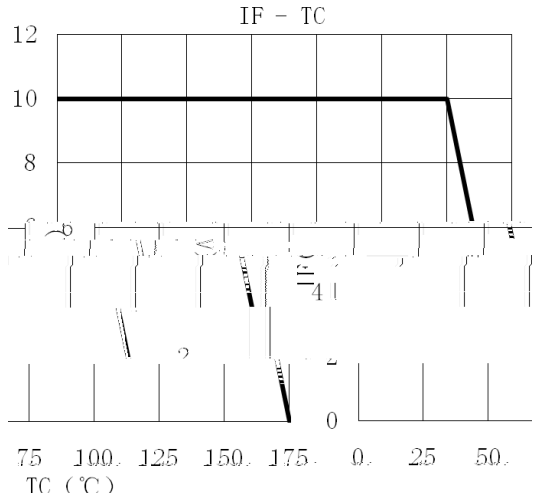


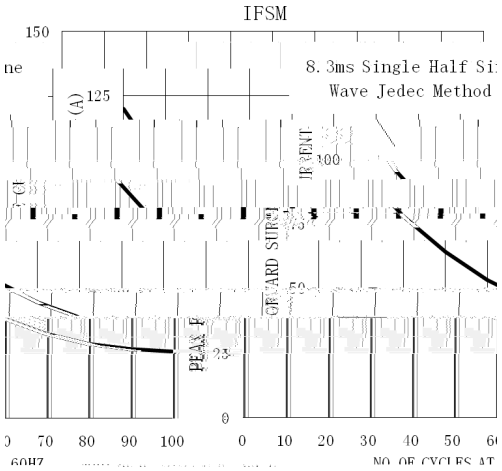
PIN1 Anode PIN 2 Cathode PIN 3 Anode

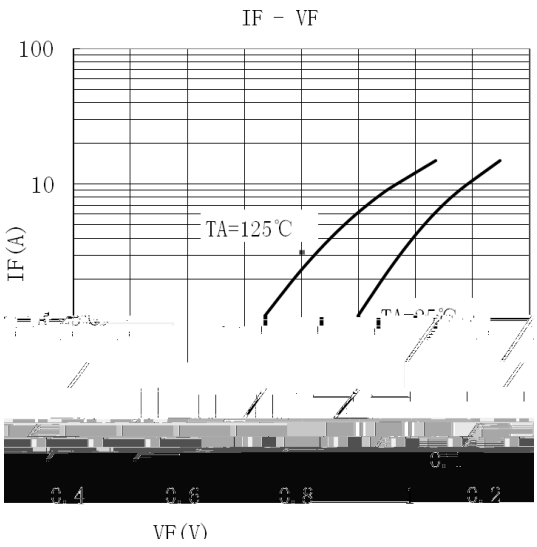
See Marking Instructions.

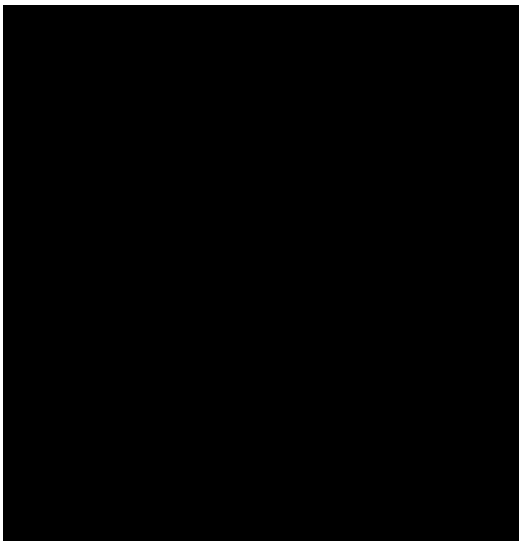
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Peak Repetitive Forward Current	$I_{F(AV)}$	10	A
Average Rectified Forward Current	I_{FRM}	10	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	150	A
Repetitive Peak Reverse Surge Current	I_{RRM}	0.5	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.5	/W
Junction and Storage Temperature Range	T_j,T_{stg}	-55 150	

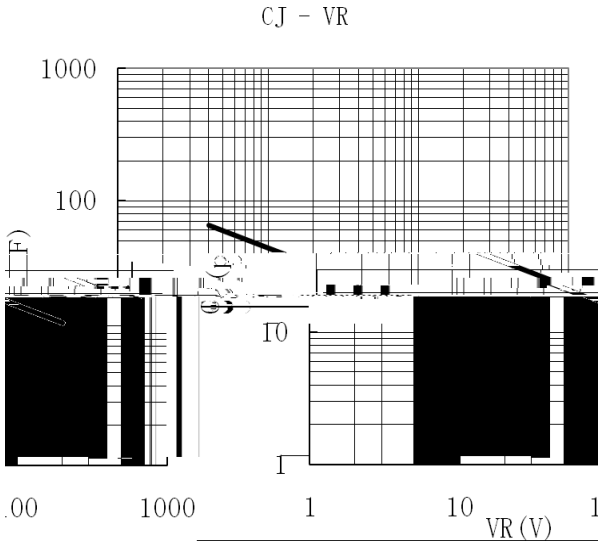
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Current Voltage	V_R		200			V
Forward Voltage	V_F	I_F=5A			0.99	V
		I_F=5A(Tc=125)			0.87	V
Instantaneous Reverse Current	I_R	V_R=200V			0.15	mA
		V_R=200V(Tc=125)			150	mA
Voltage Rate of Change	dv/dt				10000	V/μs

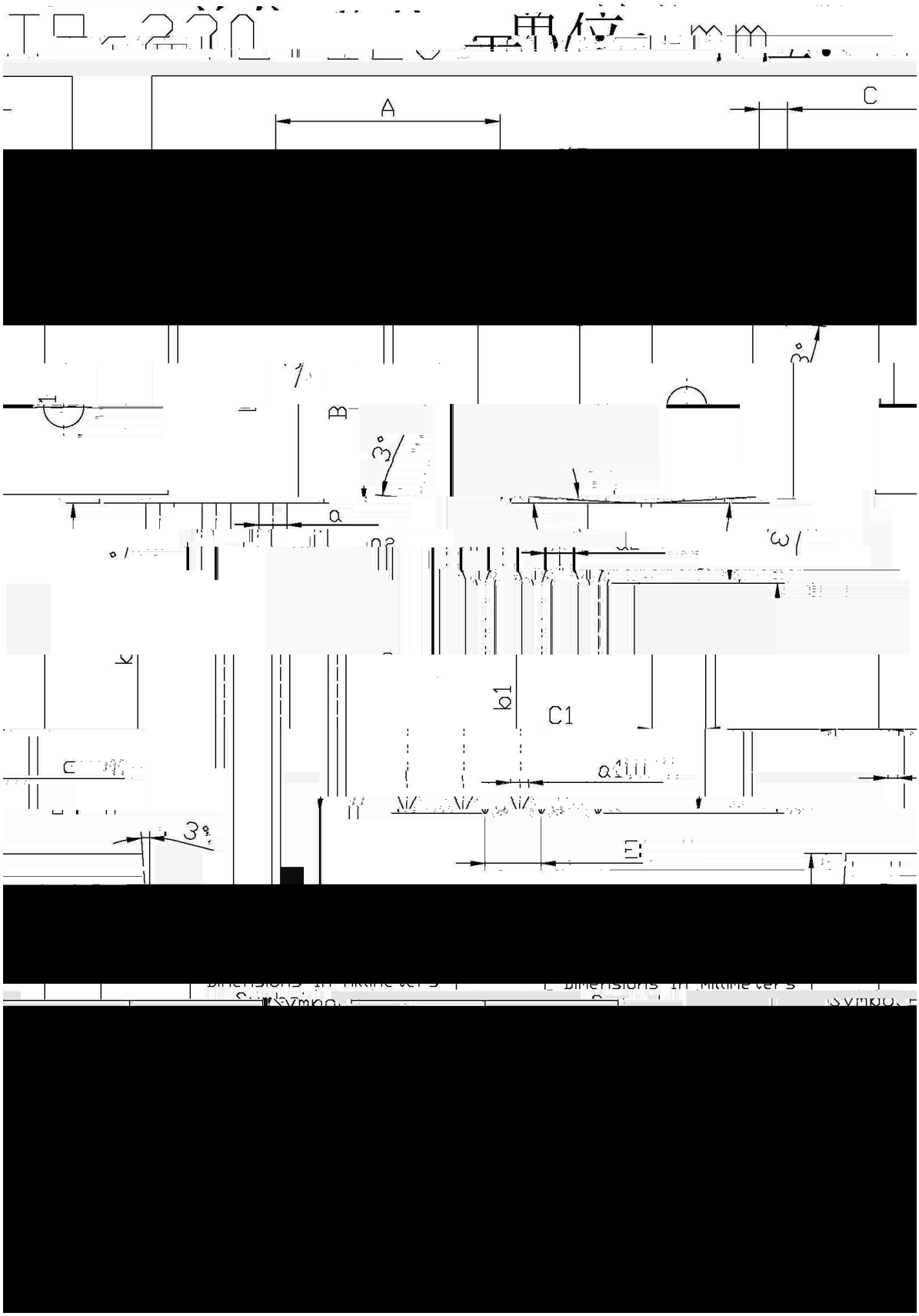

IF - TC
12
10
8
0
75 100 125 150 175 0 25 50
TC (℃)

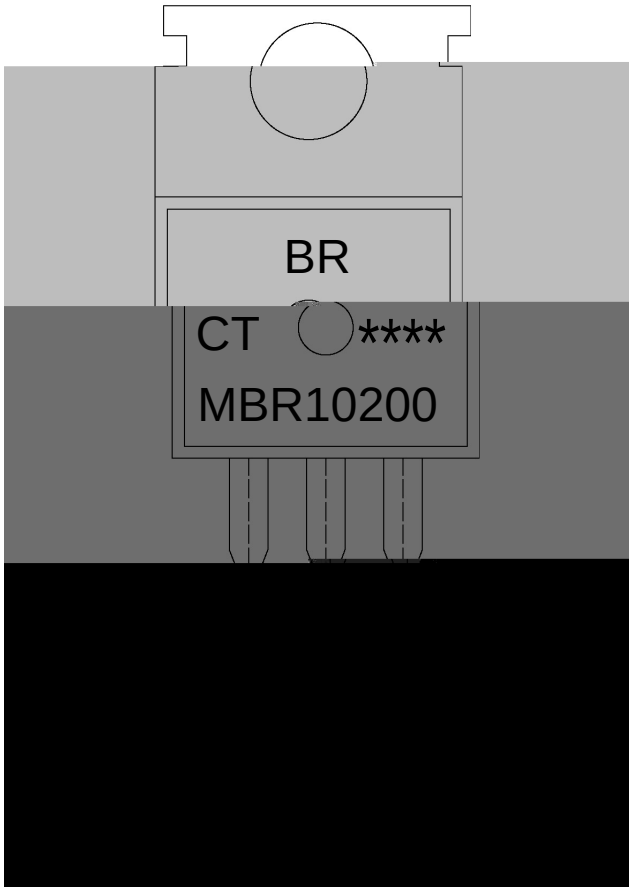

IFSM
150
125
100
8.3ms Single Half Si
Wave Jedec Method
70 80 90 100
0 10 20 30 40 50


IF - VF
100
10
IF(A)
TA=125℃
VF(V)




CJ - VR
1000
100
1000
1
10
VR(V)


A
C
B
3°
a
b1
C1
a1
E1
3°



Note:

BR:	Company Code
MBR10200	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.